

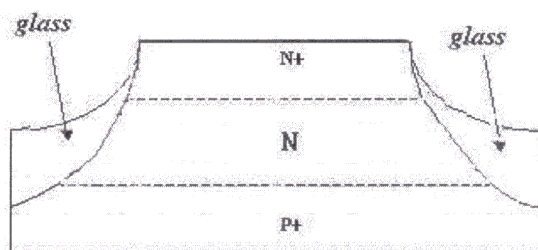
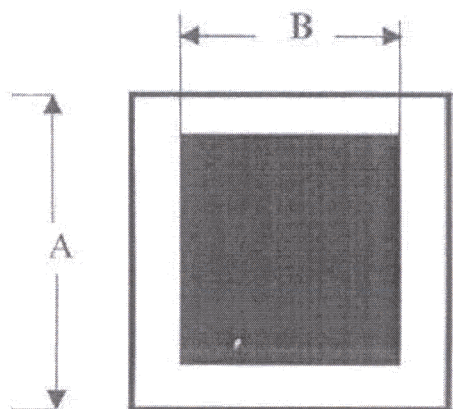
Chip Specification

General Description:

SILICON GLASS PASSIVATED CHIP STRUCTURE

MECHANICAL DATA

ITEM	DIM	mkm
Die Size 88 mil	Ax	88+/-2
	Ay	88+/-2
	Bx	70+/-2
	By	70+/-2
Thickness	(min)	240+/-2um
	(max)	
Metallization	N+ Surface metallization : Nickel and Gold P+ Surface metallization : Nickel	



CODIGO: DAC-PL-1612

VERSION: 00

No. PARTE: 1895

ELECTRICAL CHARACTERISTICS	SYM		Die Sort	Unit	Trr
DC Blocking Voltage @ 5uA	VRRM	>400	≥ 440	Volt	>1200nS
Max Instantaneous Forward Voltage @ 3A	VFM	<0.98	≤ 0.97	Volt	
Max Reverse Leakage Current @ VR= 400V	IRM	≤ 2	≤ 1	uA	

MAXIMUM RATINGS	SYM	Spec.Limit	Unit	Note
Average Forward Current	IFAV	3	Amp	2
Nonrepetitive Peak Surge Current	IFSM	100	Amp	3
Operationm Junction Temperature	Tj	-40 - +150	Degrees C	

Notes.

1. VFM is controlled on wafers in mode IF=1A
2. It is quaranteed after assembly
3. Preliminary value. Concrete value depends on type of the case and quality of assembly. It is established by results of tests of finished products at the consumer